

SMALL SIGNAL SCHOTTKY DIODES

SOD-123

FEATURES

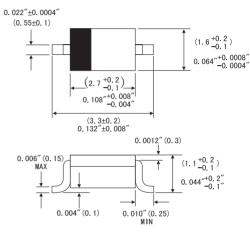
- · For general purpose applications
- These diodes features very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- This diode is also available in the Mini-MELF case with the type designation LL46 and in the DO-35 case with the type designation BAT46, in the Micro-MELF case with type designation MCL46

MECHANICAL DATA

· Case: SOD-123 plastic case

· Weight: Approx. 0.01 gram

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Dimensions in inches and (millimeters)

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units	
Repetitive Peak Reverse Voltage	VRRM	100	V	
Forward Continuous Current at TA=25°C	l _F	150 ¹⁾	mA	
Repetitive Peak Forward Current at t_p < 1s, δ <0.5, T_A =25°C	İFRM	350 ¹⁾	mA	
Surge forward current at $t_P < 10 \text{mS}$, $T_A = 25^{\circ}\text{C}$	IFSM	750 ¹⁾	mA	
Power Dissipation ¹⁾ at Ta=65°C	Ptot	150 ¹⁾	mW	
Junction temperature	TJ	125	°	
Ambient Operating temperature Range	TA	-65 to+125	°C	
Storage Temperature Range	Tstg	-65 to+150	°C	
1) Valid provided that electrodes are kept at ambient temperature				



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ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

	Symbols	Min.	Тур.	Max.	Unis
Reverse breakdown voltage Tested with 100µA Pulses	V _{(BR)R}	100			V
Forward voltage Pulse Test $t_p < 300 \mu s$, at $V_R = 10 V$, $T_J = 60$ °C , $\delta < 2\%$ at $t_R = 0.1 m A$, at $t_R = 10 m A$, at $t_R = 250 m A$	VF VF VF			0.25 0.45 1	V V
Leakage current pulse test $t_{\rm p} < 300 \mu s$, $\delta < 2\%$ at $V_{\rm R} = 1.5 V$, at $V_{\rm R} = 1.5 V$, $T_{\rm J} = 60^{\circ} {\rm C}$ at $V_{\rm R} = 10 V$ at $V_{\rm R} = 10 V$, $T_{\rm J} = 60^{\circ} {\rm C}$ at $V_{\rm R} = 50 V$, $T_{\rm J} = 60^{\circ} {\rm C}$ at $V_{\rm R} = 50 V$, $T_{\rm J} = 60^{\circ} {\rm C}$ at $V_{\rm R} = 50 V$, $T_{\rm J} = 60^{\circ} {\rm C}$ at $V_{\rm R} = 75 V$ at $V_{\rm R} = 75 V$, $T_{\rm J} = 60^{\circ} {\rm C}$	IR IR IR IR IR IR IR			0.5 5 0.8 7.5 2 15 5	µА µА µА µА µА µА µА
Junction Capacitance at VR=0V ,f=1MHz at VR=1V ,f=1MHz	C1 C1		10 6		pF pF
Thermal resistance junction to ambient Air	Røja			300 1)	K/W